

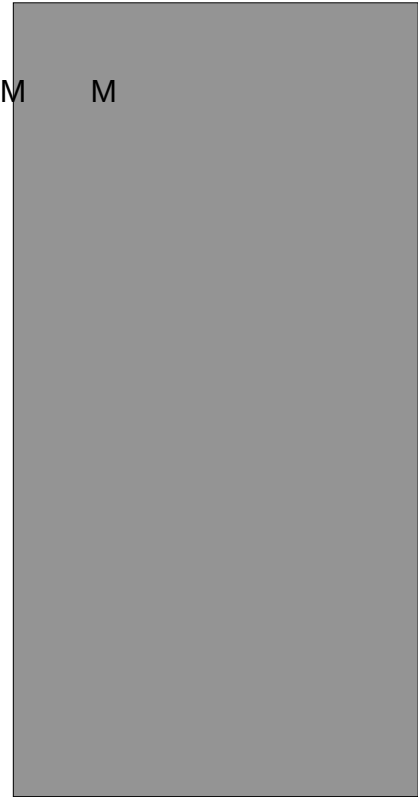


JCT640FH 40A SCR

Rev.A.1.1

CT640F . S onides h w e ts t rinn 9 onad c a

With high ability to withstand the shock loading of large current, JCT640FH SCR provides high dV/dt rate with strong resistance to eCO





Peak gate current ($t_p=20\mu s$, $T_j=150$)	I_{GM}	10	A
Average gate power dissipation ($T_j=150$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	0.5	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V$ $R_L=33\Omega$	-	-	35	mA
V_{GT}		-	-	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150$ $R_L=3.3k\Omega$	0.2	-	-	V
I_L	$I_G=1.2I_{GT}$	-	-	80	mA
I_H	$I_T=500mA$	-	-	70	mA
dV/dt	$V_D=400V$ Gate Open $T_j=125$	1300	-	-	V/ μs
	$V_D=400V$ Gate Open $T_j=150$	700	-	-	
t_{on}	$I_G=40mA$ $I_A=400mA$ $I_R=40mA$ $T_j=25$	-	2	-	μs
t_{off}		-	60	-	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=80A$ $t_p=380\mu s$	$T_j=25$	1.55	V
V_{TO}	Threshold voltage	$T_j=150$	0.65	V
R_D	Dynamic resistance	$T_j=150$	17	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=150$	8	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	2.58	/W
$R_{th(j-a)}$	junction to ambient (DC)	60	/W





FIG.1: Maximum power dissipation versus RMS on-state current

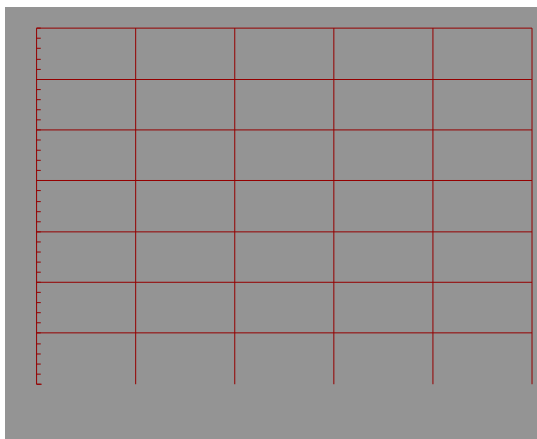
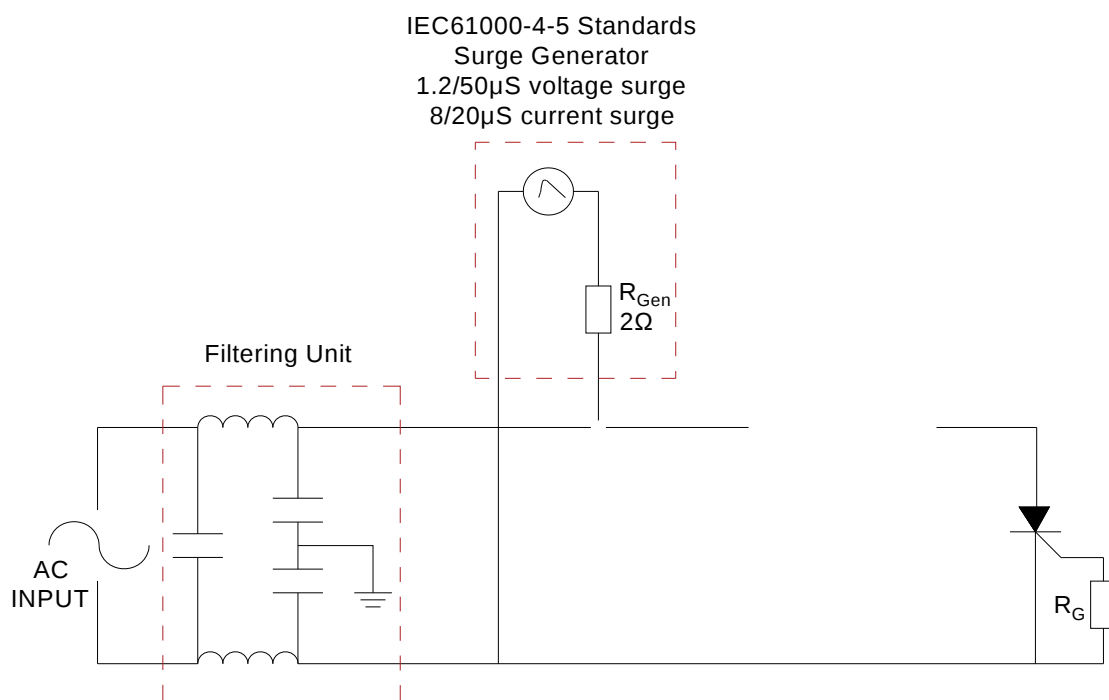


FIG.2: RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT640FH	600	35	TO-220F(Ins)	50	Tube

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Document Revision History

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